
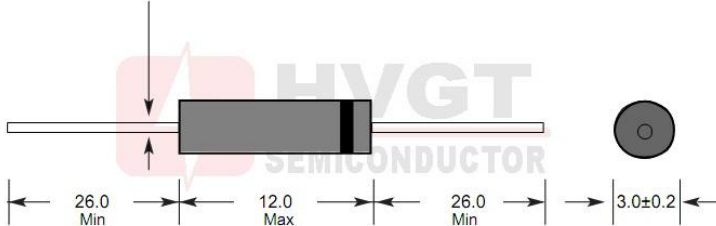




INTRODUCE: HVGT high voltage silicon rectifier diodes is made of high quality glass passivated chip and high reliability epoxy resin sealing structure, and through professional testing equipment inspection qualified after to customers.	SHAPE DISPLAY: 
FEATURES: 1. High reliability design. 2. High voltage design. 3. High frequency . 4. Conform to RoHS. 5. Epoxy resin molded in vacuumHave anticorrosion in the surface.	SIZE: (Unit:mm) : HVGT NAME: DO-312
APPLICATIONS: 1. High voltage multiplier circuit 2. Electrostatic generator circuit . 3. General purpose high voltage rectifier. 4. Other.	DO-312 Series Lead Diameter 0.6mm 
MECHANICAL DATA: 1. Case: epoxy resin molding. 2. Terminal: welding axis. 3. Net weight: 0.30 grams (approx).	Unit:mm

MAXIMUM RATINGS AND CHARACTERISTICS: (Absolute Maximum Ratings)

Items	Symbols	Condition	Data Value	Units
Repetitive Peak Reverse Voltage	V_{RRM}	$T_A=25^{\circ}C$	20	kV
Average Forward Current Maximum	I_{FAVM}	$T_A=25^{\circ}C$	5.0	mA
		$T_{OIL}=-^{\circ}C$	--	mA
Suege Current	I_{FSM}	$T_A=25^{\circ}C$; Half-Sine Wave; 8.3mS	0.5	A
Junction Temperature	T_J		-40~+125	$^{\circ}C$
Allowable Operation Case Temperature	T_C		125	$^{\circ}C$
Storage Temperature	T_{STG}		-40~+125	$^{\circ}C$

ELECTRICAL CHARACTERISTICS: $T_A=25^{\circ}C$ (Unless Otherwise Specified)

Items	Symbols	Condition	Data value	Units
Maximum Forward Voltage Drop	V_F	at $25^{\circ}C$; at $I_{F(AV)}$	45	V
Maximum Reverse Current	I_{R1}	at $25^{\circ}C$; at V_{RRM}	2.0	μA
	I_{R2}	at $100^{\circ}C$; at V_{RRM}	5.0	μA
Maximum Reverse Recovery Time	T_{RR}	at $25^{\circ}C$; $I_F=0.5I_R$; $I_R=I_{FAVM}$; $I_{RR}=0.25I_R$	100	nS
Junction Capacitance	C_J	at $25^{\circ}C$; $V_R=0V$; $f=1MHz$	1.0	pF



Fig1

Forward Characteristics

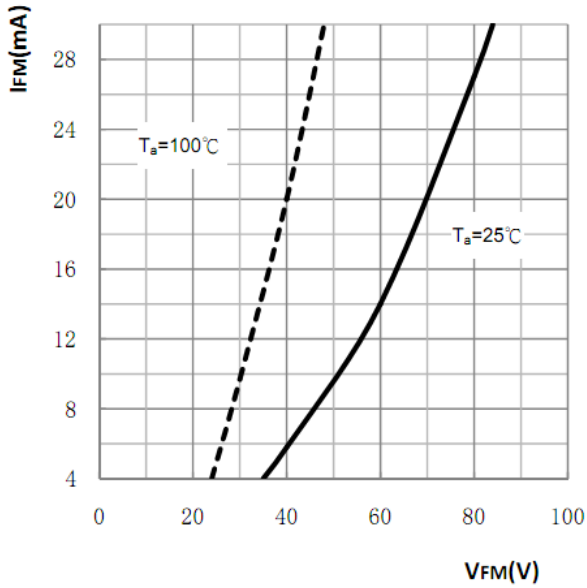


Fig2

Reverse Characteristics

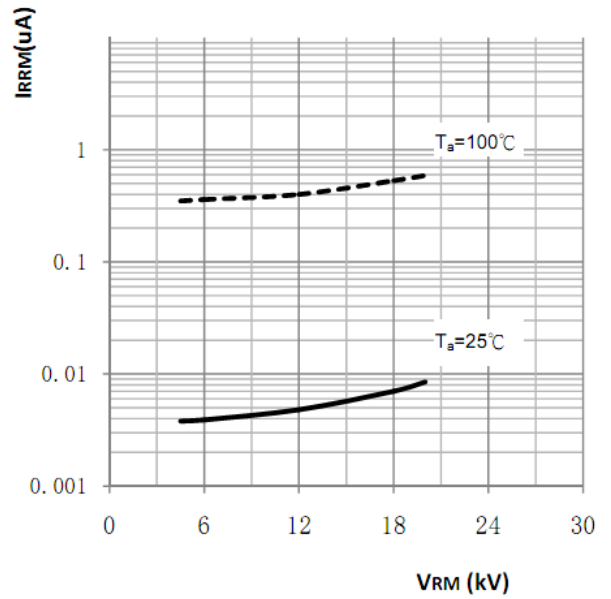


Fig3

VR-IF(AV) Curve

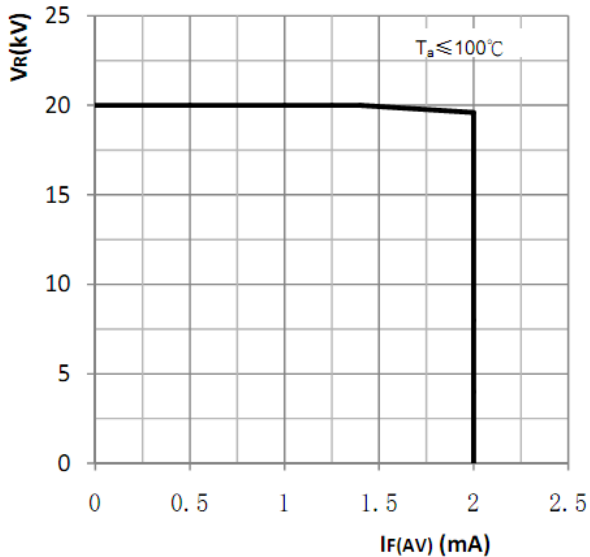
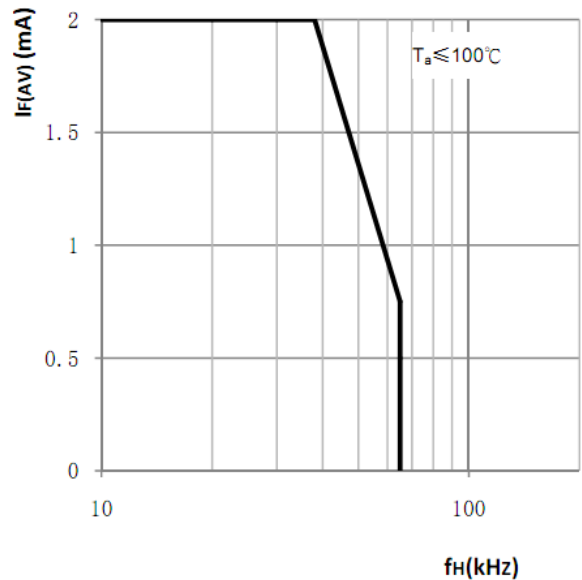


Fig4

IF(AV)-fH Curve



Marking

Type

2CL77

Code

Cathode Mark

